

MOSFETs Silicon N-Channel MOS

SSM3K2615TU

1. Applications

- · Load Switches
- · Motor Drivers

2. Features

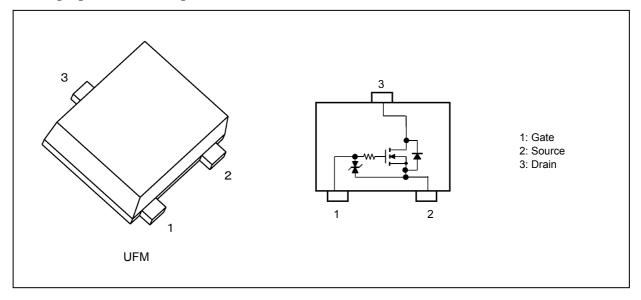
- (1) AEC-Q101 Qualified (Note1).
- (2) 3.3-V gate drive voltage.
- (3) Low drain-source on-resistance
 - : $R_{DS(ON)}$ = 380 m Ω (typ.) (@ V_{GS} = 3.3 V, I_D = 0.5 A)

 $R_{DS(ON)} = 330 \text{ m}\Omega \text{ (typ.) } (@V_{GS} = 4.0 \text{ V}, I_D = 1.0 \text{ A})$

 $R_{\rm DS(ON)}$ = 230 mO (typ.) (@V_{\rm GS} = 10 V, $I_{\rm D}$ = 1.0 A)

Note1: For detail information, please contact to our sales.

3. Packaging and Pin Assignment





4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

Characteristic	s		Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	60	V
Gate-source voltage	'		V_{GSS}	±20	
Drain current (DC)		(Note 1)	I_D	2	Α
Drain current (pulsed)		(Note 1), (Note 2)	I _{DP}	6	
Power dissipation	'	(Note 3)	P_{D}	0.8	W
Power dissipation	(t = 10 s)	(Note 3)	P_{D}	1.6	
Channel temperature			T _{ch}	150	°C
Single-pulse avalanche energy		(Note 4)	E _{AS}	52.9	mJ
Avalanche current			I _{AR}	2	Α
Storage temperature			T _{stg}	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW) \leq 10 ms, duty \leq 1%
- Note 3: Device mounted on an FR4 board. (25.4 mm × 25.4 mm × 1.6 mm ,Cu pad: 645 mm²)
- Note 4: V_{DD} = 25 V, T_{ch} = 25°C (Initial state), L = 20 mH, R_G = 25 Ω , I_{AR} = 2A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

Note: The channel-to-ambient thermal resistance, R_{th(ch-a)}, and the drain power dissipation, P_D, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



5. Electrical Characteristics

5.1. Static Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 16 \text{ V}$	_	_	±10	μА
Drain cut-off current		I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	_	_	1	
Drain-source breakdown voltage		V _{(BR)DSS}	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	60	_		V
Gate threshold voltage	(Note 1)	V_{th}	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	0.8	_	2.0	V
Drain-source on-resistance	(Note 2)	R _{DS(ON)}	$I_D = 0.5 \text{ A}, V_{GS} = 3.3 \text{ V}$	_	0.38	0.58	Ω
			I _D = 1.0 A, V _{GS} = 4.0 V	_	0.33	0.44	
			I _D = 1.0 A, V _{GS} = 10 V	_	0.23	0.30	
Forward transfer admittance	(Note 2)	Y _{fs}	V _{DS} = 10 V, I _D = 1.0 A	1.0	2.0	_	S

Note 1: Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (1 mA for this device). Then, for normal switching operation, $V_{GS(ON)}$ must be higher than V_{th} , and $V_{GS(OFF)}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$.

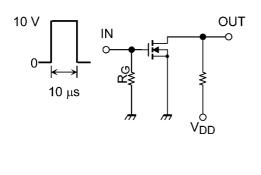
Take this into consideration when using the device.

Note 2: Pulse measurement.

5.2. Dynamic Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$	_	150	_	pF
Reverse transfer capacitance	C _{rss}	f = 1 MHz	_	25	_	
Output capacitance	C _{oss}		_	70	_	
Switching time (rise time)	t _r	$V_{DD} \approx 30 \text{ V}, I_D = 1 \text{ A}$	_	25	_	ns
Switching time (turn-on time)	t _{on}	V_{GS} = 0 to 10 V, R_G = 50 Ω	_	30	_	
Switching time (fall time)	t _f		_	50	_	
Switching time (turn-off time)	t _{off}		_	150	_	

5.3. Switching Time Test Circuit



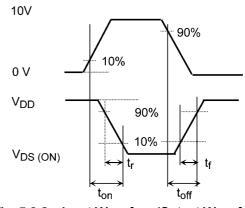


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

5.4. Gate Charge Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx 48 \text{ V}, V_{GS} = 10 \text{ V},$	_	6.0		nC
Gate-source charge 1	Q _{gs1}	I _D = 2.0 A	_	0.5		
Gate-drain charge	Q _{gd}		_	1.4	_	



5.5. Source-Drain Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 1)	I _{DR}	_	_	_	2	Α
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	_	_	_	6	Α
Diode forward voltage	(Note 2)	V _{DSF}	I _D = -2.0 A, V _{GS} = 0 V	_	-0.9	-1.5	V
Reverse recovery time		t _{rr}	I _{DR} = 2 A, V _{GS} = 0 V,	_	100	_	ns
Reverse recovery charge		Q _{rr}	dl _{DR} /dt = 50 A/μs	_	40	_	nC

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Pulse measurement.

6. Marking

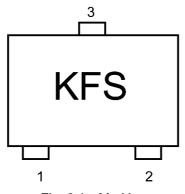


Fig. 6.1 Marking

7. Characteristics Curves (Note)

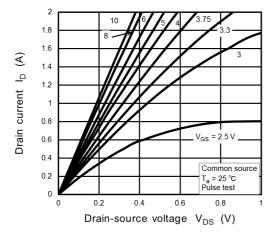


Fig. 7.1 I_D - V_{DS}

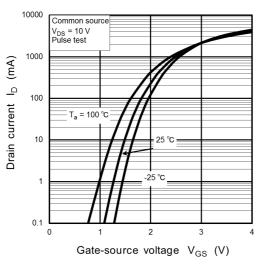


Fig. 7.3 I_D - V_{GS}

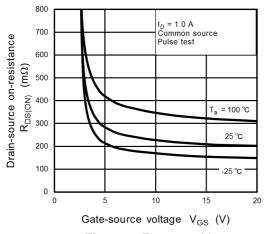


Fig. 7.5 R_{DS(ON)} - V_{GS}

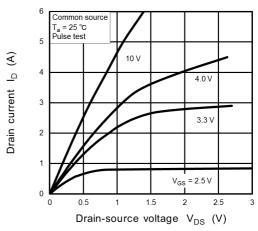


Fig. 7.2 $I_D - V_{DS}$

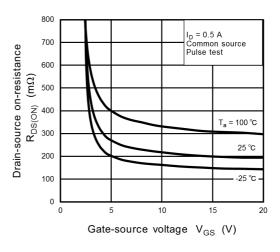


Fig. 7.4 R_{DS(ON)} - V_{GS}

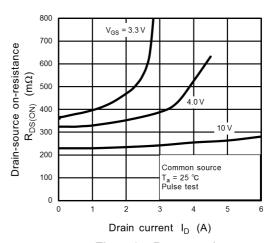


Fig. 7.6 $R_{DS(ON)}$ - I_D

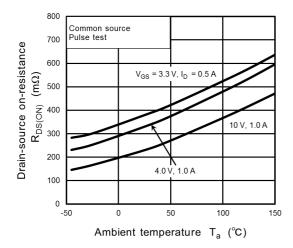
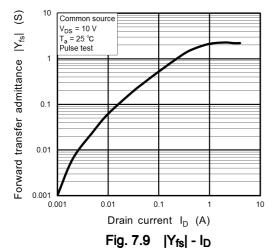


Fig. 7.7 R_{DS(ON)} - T_a



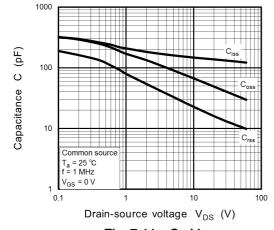


Fig. 7.11 C - V_{DS}

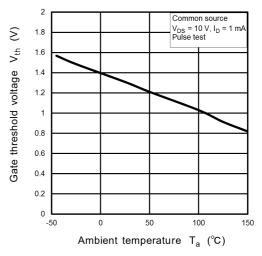


Fig. 7.8 V_{th} - T_a

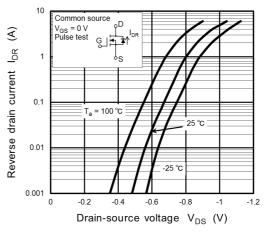


Fig. 7.10 I_{DR} - V_{DS}

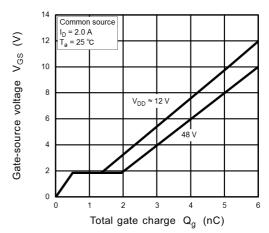


Fig. 7.12 Dynamic Input Characteristics

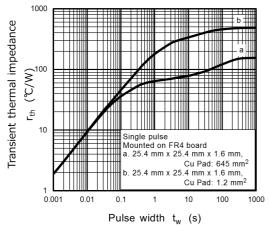


Fig. 7.13 r_{th} - t_w

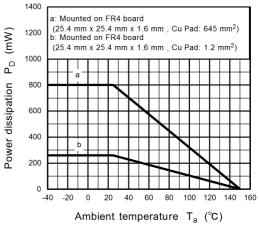


Fig. 7.14 P_D - T_a

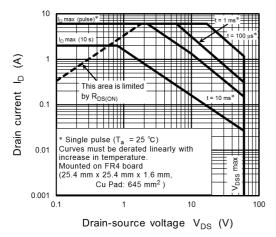


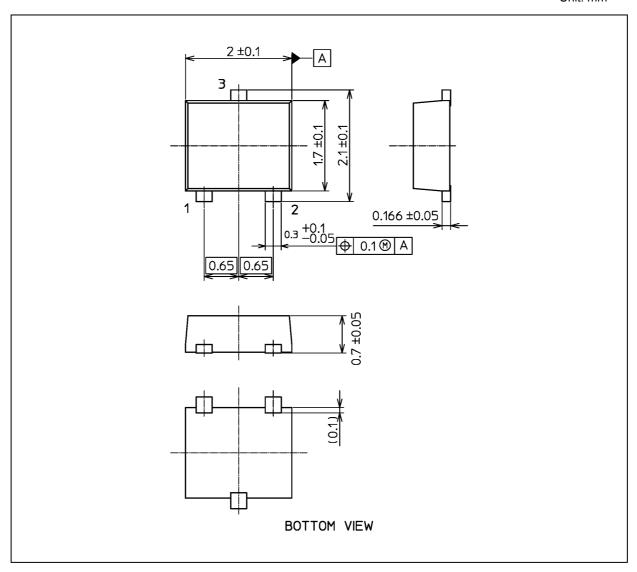
Fig. 7.15 Safe Operating Area

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 6.6 mg (typ.)

	Package Name(s)	
Nickname: UFM		

Rev.2.0



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